



SEMITRANS® 2

Superfast NPT-IGBT Modules

SKM50GB063D

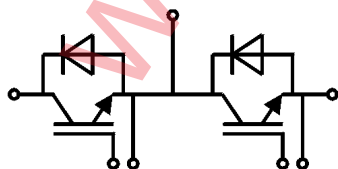
Target Data

Features

- NPT = non punch-through IGBT technology
- High short circuit capability, self limiting to 6 x IC
- Pos. temp.-coeff. of VCEsat
- Isolated copper baseplate

Typical Applications*

- Switched mode power supplies
- UPS
- Three phase inverters for servo / AC motor speed control



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Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V _{CES}	T _j = 25 °C		600	V
I _C	T _j = 150 °C	T _c = 25 °C	70	A
		T _c = 75 °C	51	A
I _{Cnom}			50	A
I _{CRM}	I _{CRM} = 2xI _{Cnom}		100	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 300 V V _{GE} ≤ 20 V V _{CES} ≤ 600 V	T _j = 125 °C	10	µs
T _j			-55 ... 150	°C
Inverse diode				
I _F		T _c = 25 °C	75	A
		T _c = 80 °C	45	A
I _{Fnom}			50	A
I _{FRM}	I _{FRM} = 2xI _{Fnom}		100	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C			A
T _j			-40 ... 150	°C
Module				
I _{t(RMS)}	T _{terminal} < 80 °C		200	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50Hz, t = 1 min		2500	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
V _{CE(sat)}	I _C = 50 A	T _j = 25 °C		2.1	2.5	V
	V _{GE} = 15 V chiplevel	T _j = 125 °C		2.4	2.8	V
V _{CE0}		T _j = 25 °C		1.05	1.3	V
		T _j = 125 °C		1	1.2	V
r _{CE}	V _{GE} = 15 V	T _j = 25 °C		21.0	24.0	mΩ
		T _j = 125 °C		28.0	32.0	mΩ
V _{GE(th)}	V _{GE} =V _{CE} , I _C = 1 mA		4.5	5.5	6.5	V
I _{CES}	V _{GE} = 0 V	T _j = 25 °C		0.1	0.3	mA
	V _{CE} = 600 V					mA
C _{ies}	V _{CE} = 25 V	f = 1 MHz		2.2		nF
C _{oes}	V _{GE} = 0 V	f = 1 MHz				nF
C _{res}		f = 1 MHz		0.2		nF
Q _G	V _{GE} = - 8 V...+ 20 V					nC
R _{Gint}	T _j = 25 °C					Ω
t _{d(on)}	V _{CC} = 300 V	T _j = 125 °C		50		ns
t _r	I _C = 50 A	T _j = 125 °C		40		ns
E _{on}	V _{GE} = ±15 V	T _j = 125 °C		2.5		mJ
	R _{G on} = 22 Ω	T _j = 125 °C				
t _{d(off)}	R _{G off} = 22 Ω	T _j = 125 °C		300		ns
t _f		T _j = 125 °C		30		ns
E _{off}		T _j = 125 °C		1.8		mJ
R _{th(j-c)}	per IGBT				0.5	K/W



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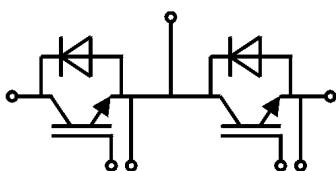
Features

- NPT = non punch-through IGBT technology
- High short circuit capability, self limiting to 6 x IC
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Typical Applications*

- Switched mode power supplies
- UPS
- Three phase inverters for servo / AC motor speed control

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
V _F = V _{EC}	I _F = 50 A	T _j = 25 °C		1.35	1.60	V
	V _{GE} = 0 V chip	T _j = 125 °C		1.35	1.60	V
V _{F0}		T _j = 25 °C		1.05	1.2	V
		T _j = 125 °C		0.9	1	V
r _F		T _j = 25 °C		6.0	8.0	mΩ
		T _j = 125 °C		9.0	12.0	mΩ
I _{RRM}	I _F = 50 A	T _j = 125 °C		31		A
Q _{rr}	di/dt _{off} = 50 A/μs	T _j = 125 °C		3.2		μC
E _{rr}	V _{GE} = ±15 V V _{CC} = 300 V	T _j = 125 °C		0.48		mJ
R _{th(j-c)}	per diode				1	K/W
Module						
L _{CE}					30	nH
R _{CC'+EE'}	terminal-chip	T _C = 25 °C		0.65		mΩ
		T _C = 125 °C		1		mΩ
R _{th(c-s)}	per module			0.04	0.05	K/W
M _s	to heat sink M6		3		5	Nm
M _t		to terminals M5	2.5		5	Nm
						Nm
w					160	g



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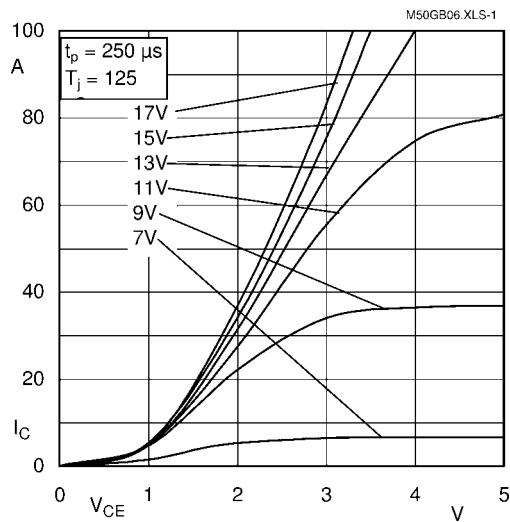


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

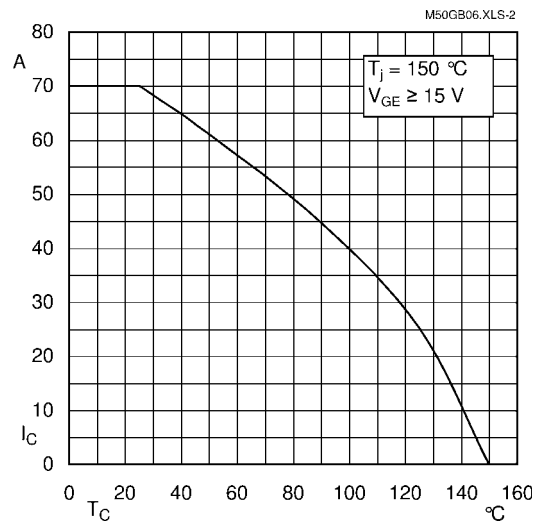


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

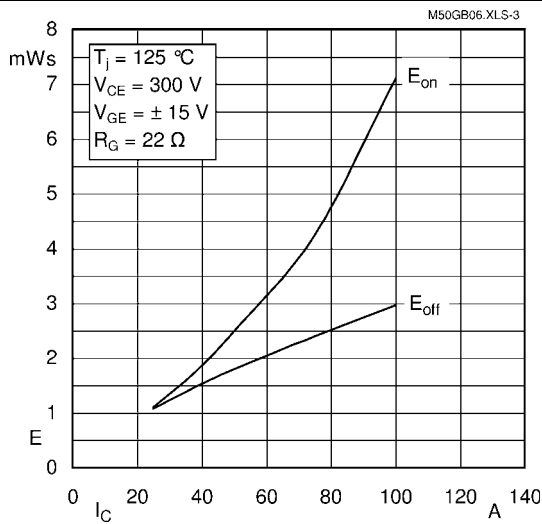


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

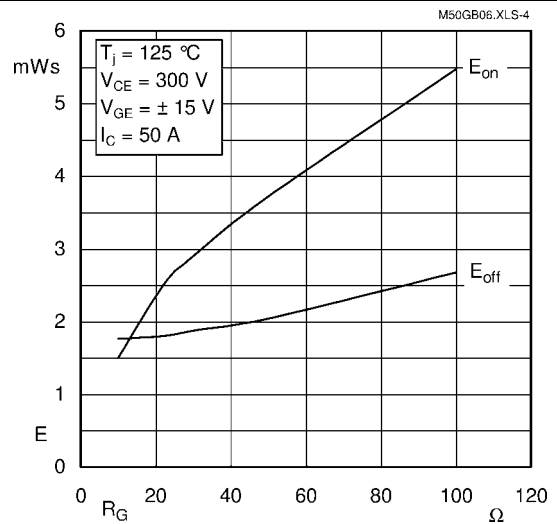


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

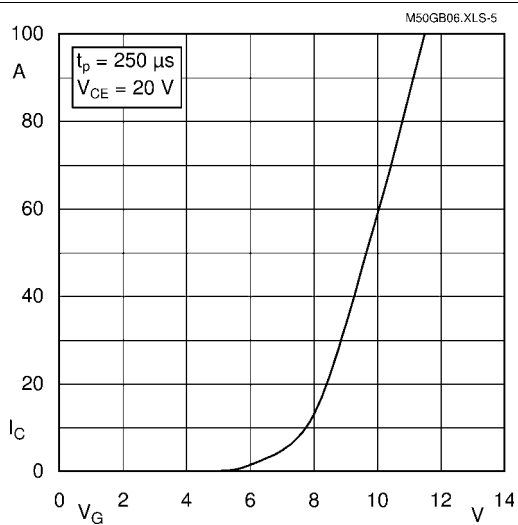


Fig. 5: Typ. transfer characteristic

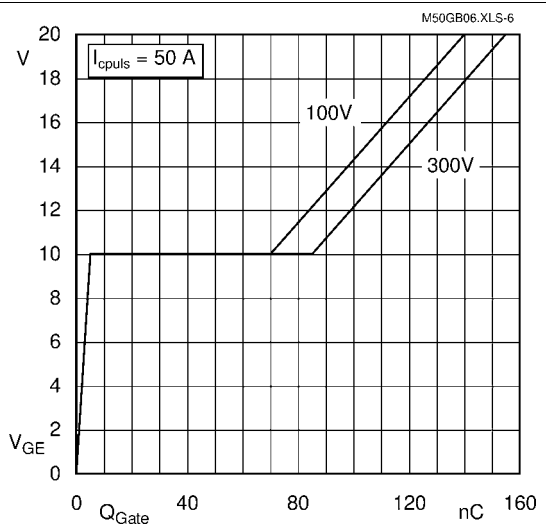


Fig. 6: Typ. gate charge characteristic

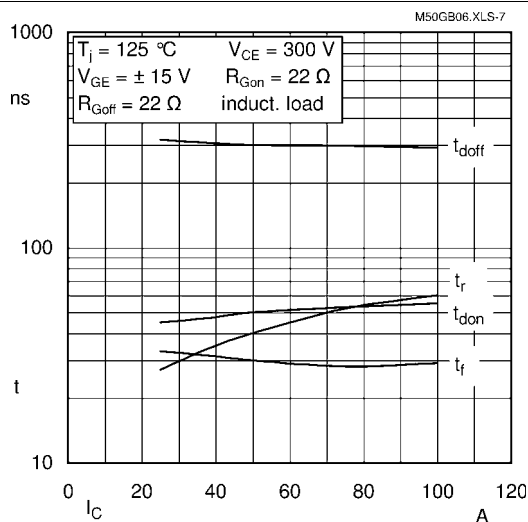


Fig. 7: Typ. switching times vs. I_C

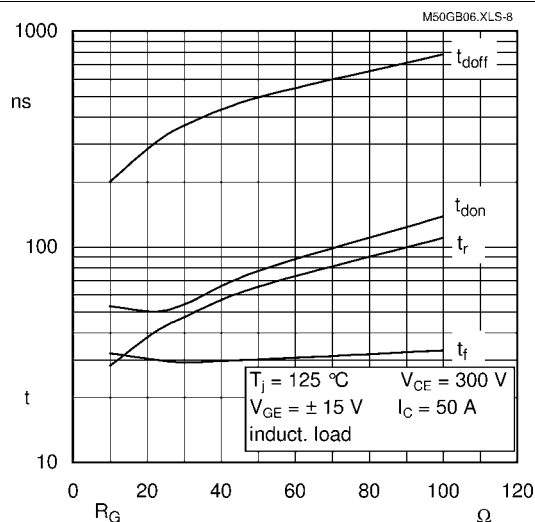


Fig. 8: Typ. switching times vs. gate resistor R_G

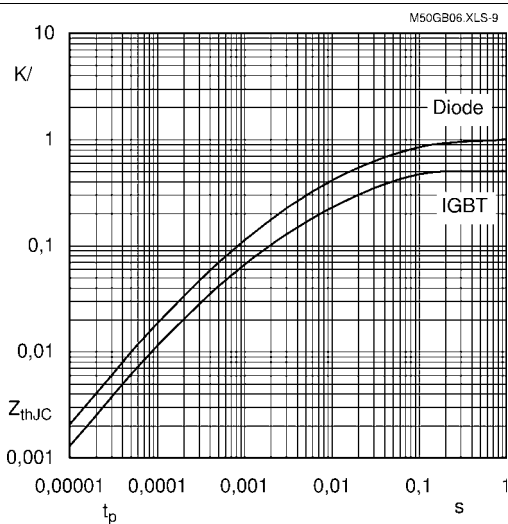


Fig. 9: Transient thermal impedance

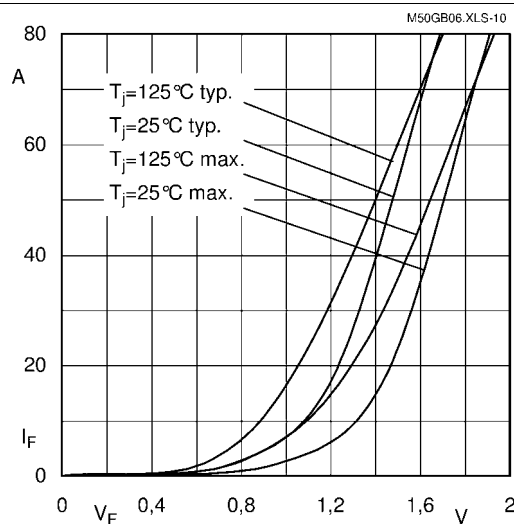


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+EE'}$

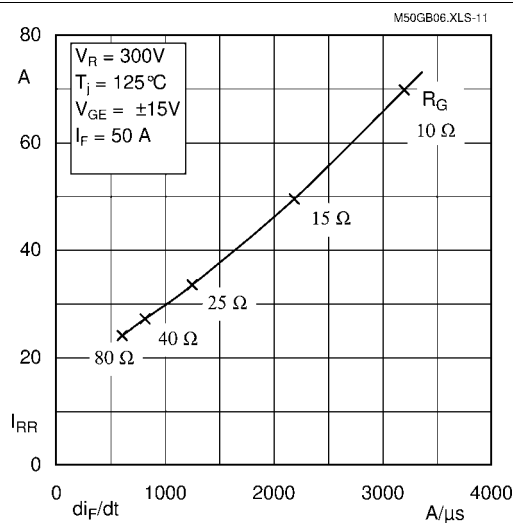


Fig. 11: CAL diode peak reverse recovery current

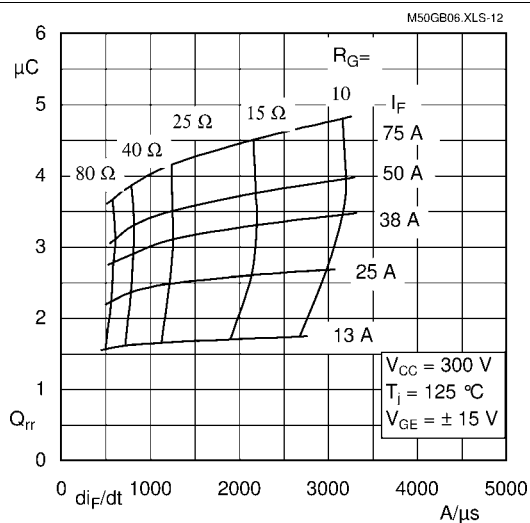
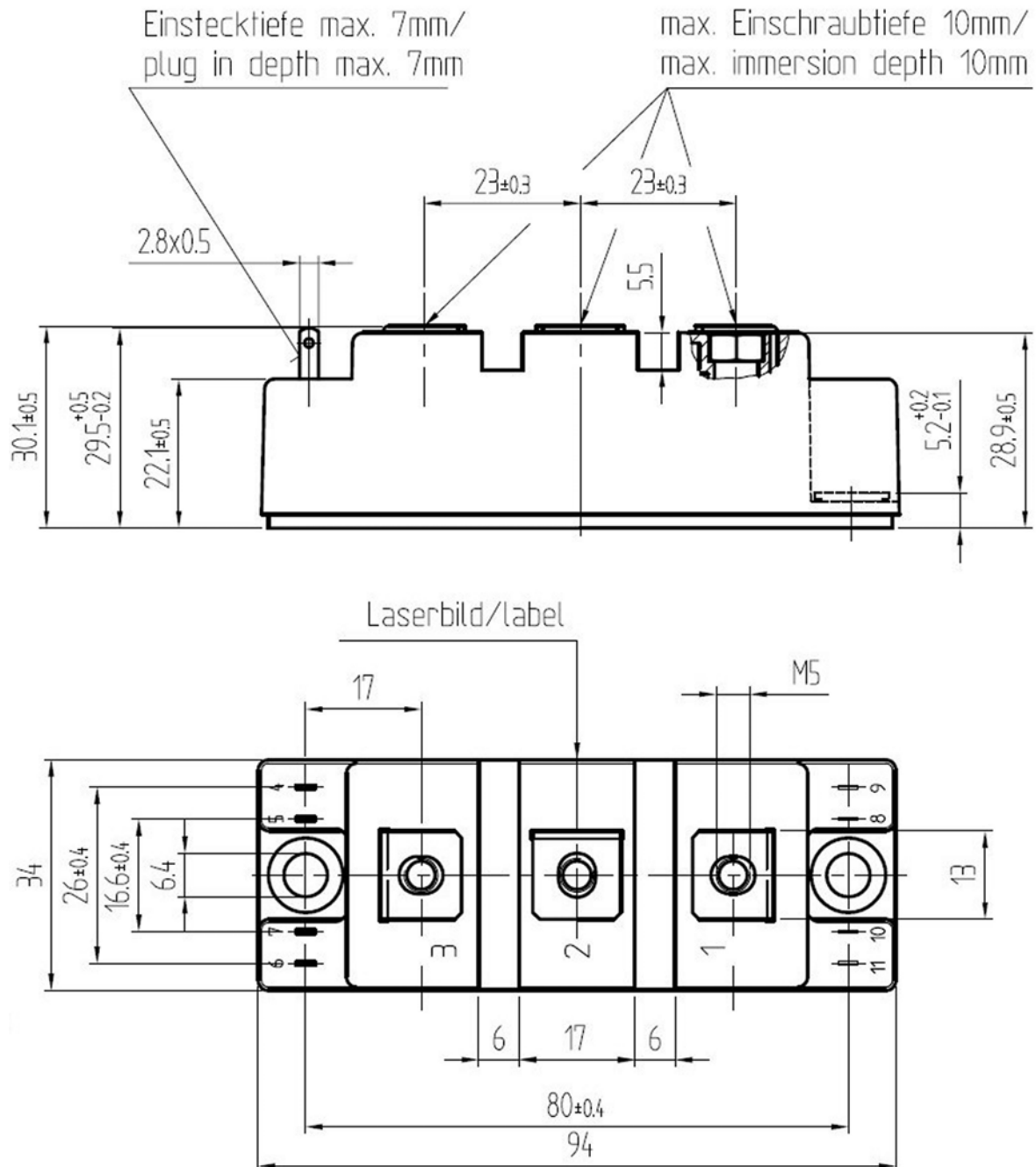
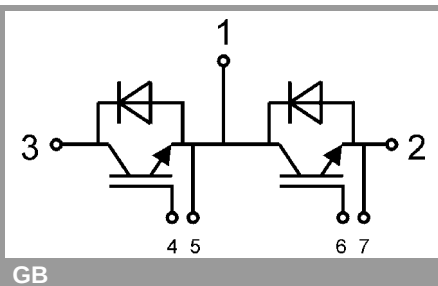


Fig. 12: Typ. CAL diode peak reverse recovery charge



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.